

PIN CONFIGURATION 36-Pin SOJ

A4 [1 • · · · ·	36 🛛 NC
A3 [2	35 🗋 A5
A2 [3	34 🗋 A6
A1 [4	33 🗍 A7
A0 [5	32 🗋 A8
CE	6	31 🗍 OE
I/O0 [7	30 🗍 1/07
I/O1 [8	29 🗍 1/06
VDD	9	28 🗍 GND
GND [10	27 🛛 Vdd
I/O2	11	26 🗍 1/O5
I/O3 [12	25 🗍 1/04
WE	13	24 🗋 A9
A17 [14	23 🗍 A10
A16 [15	22 🗍 A11
A15 [16	21 🛛 A12
A14 [17	20 🗍 NC
A13 [18	19 🛛 NC
	L]

NC 🔲 1 🌑	44 🗖 NC
NC 🗖 2	43 🗖 NC
A4 🔲 3	42 🗖 NC
A3 🗖 4	41 🗖 A5
A2 🗖 5	40 🗖 A6
A1 🗖 6	39 🗖 A7
A0 🔲 7	38 🗖 🗛
CE 🔲 8	37 🗖 ŌĒ
I/O0 🔲 9	36 🔲 1/07
I/O1 🔲 10	35 🗖 1/O6
Vdd 🔲 11	34 🗖 GND
GND 🔲 12	33 🗖 VDD
I/O2 🔲 13	32 🗖 1/O5
I/O3 🔲 14	31 🗖 1/O4
WE 🔲 15	30 🗖 A9
A17 🗖 16	29 🗖 A10
A16 🔲 17	28 🗖 A11
A15 🔲 18	27 🗖 A12
A14 🔲 19	26 🗖 NC
A13 🗖 20	25 🗖 NC
NC 🗖 21	24 🗖 NC
NC 🗖 22	23 🗖 NC

44-Pin TSOP (Type II)

PIN DESCRIPTIONS

A0-A17	Address Inputs
CE	Chip Enable Input
ŌĒ	Output Enable Input
WE	Write Enable Input
I/00-I/07	Bidirectional Ports
Vdd	Power
GND	Ground
NC	NoConnection

TRUTH TABLE

Mode	WE	CE	ŌĒ	I/O Operation	VDD Current	
Not Selected (Power-down)	Х	Н	Х	High-Z	ISB1, ISB2	
Output Disabled	Н	L	Н	High-Z	lcc	
Read	Н	L	L	Dout	lcc	
Write	L	L	Х	DIN	lcc	

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit	
Vdd	Supply voltage with Respect to GND	-0.5 to +4.0	V	
VTERM	Terminal Voltage with Respect to GND	-0.5 to VDD + 0.5	V	
Tstg	Storage Temperature	-65 to +150	C°	
PD	Power Dissipation	1.0	W	

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

OPERATING RANGE

Range	Ambient Temperature	Vdd (8ns)	Vdd (10 ns)	
Commercial	0°C to +70°C	3.3V +10%,-5%	3.3V <u>+</u> 10%	
Industrial	–40°C to +85°C		3.3V <u>+</u> 10%	

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Vон	Output HIGH Voltage	$V_{DD} = Min., I_{OH} = -4.0 \text{ mA}$	2.4	_	V
Vol	Output LOW Voltage	$V_{DD} = Min., I_{OL} = 8.0 mA$	—	0.4	V
Vih	Input HIGH Voltage ⁽¹⁾		2.0	Vdd + 0.3	V
VIL	Input LOW Voltage ⁽¹⁾		-0.3	0.8	V
L	InputLeakage	$GND \leq V_{IN} \leq V_{DD}$	-1	1	μA
Ilo	OutputLeakage	$GND \leq VOUT \leq VDD$, Outputs Disabled	-1	1	μA

Note:

1. $V_{IL}(min) = -0.3V (DC); V_{IL}(min) = -2.0V (pulse width - 2.0 ns).$

 $V_{H}(max) = V_{DD} + 0.3V (DC); V_{H}(max) = V_{DD} + 2.0V (pulse width - 2.0 ns).$



POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	Test Conditions		-	ns Max.		ns Max.	Unit
lcc	VDD Operating Supply Current	$V_{DD} = Max., \overline{CE} = V_{IL}$ lout = 0 mA, f = Max.	Com. Ind. typ. ⁽²⁾	_	65 50		60 65 50	mA
ISB1	TTL Standby Current (TTL Inputs)	$\label{eq:VD} \begin{array}{l} V_{\text{DD}} = Max., \\ V_{\text{IN}} = V_{\text{IH}} \text{ or } V_{\text{IL}} \\ \hline \overline{\textbf{CE}} \geq V_{\text{IH}}, \text{ f} = max \end{array}$	Com. Ind.	_	30	_	25 30	mA
ISB2	CMOS Standby Current (CMOS Inputs)	$\label{eq:vdd} \begin{array}{l} V_{DD} = Max., \\ \hline \overline{\textbf{CE}} \geq V_{DD} - 0.2V, \\ V_{IN} \geq V_{DD} - 0.2V, \text{ or} \\ V_{IN} \leq \ 0.2V, \ f = 0 \end{array}$	Com. Ind. typ. ⁽²⁾	_	3 700		3 4 700	mA mA μA

Note:

1. At f = fMAX, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.

2. Typical values are measured at VDD=3.3V, TA=25°C. Not 100% tested.

CAPACITANCE^(1,2)

Symbol F	Parameter	Conditions	Max.	Unit
Cin I	nput Capacitance	$V_{IN} = 0V$	6	pF
Ci/o I	nput/Output Capacitance	Vout = 0V	8	pF

Notes:

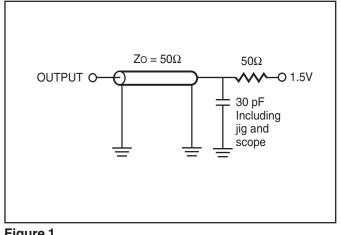
1. Tested initially and after any design or process changes that may affect these parameters.

2. Test conditions: $T_A = 25^{\circ}C$, f = 1 MHz, $V_{DD} = 3.3V$.

AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	3 ns
Input and Output Timing and Reference Levels	1.5V
OutputLoad	See Figures 1 and 2

AC TEST LOADS



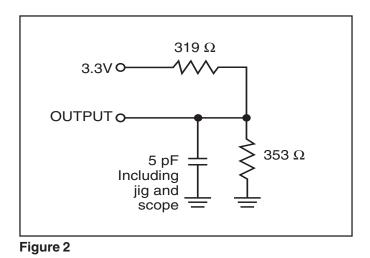


Figure 1

Integrated Silicon Solution, Inc. — www.issi.com — 1-800-379-4774 Rev. D 04/28/08

READ CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

		- 8	ns	-10	ns	
Symbol	Parameter	Min.	Мах	Min.	Max.	Unit
trc	Read Cycle Time	8	_	10	_	ns
taa	Address Access Time	_	8	_	10	ns
tона	Output Hold Time	2.5	_	2.5	_	ns
t ACE	CE Access Time	_	8	_	10	ns
t doe	OE Access Time	_	3.5	_	4	ns
tlzoe ⁽²⁾	OE to Low-Z Output	0	_	0	_	ns
thzoe ⁽²⁾	OE to High-Z Output	0	3.5	0	4	ns
tlzce ⁽²⁾	CE to Low-Z Output	3.5	_	3	_	ns
thzce ⁽²⁾	CE to High-Z Output	0	3.5	0	4	ns

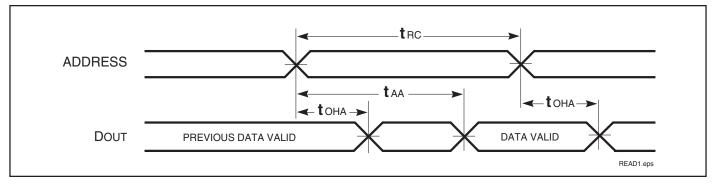
Notes:

1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1. 2. Tested with the load in Figure 2. Transition is measured ±200 mV from steady-state voltage. Not 100% tested.

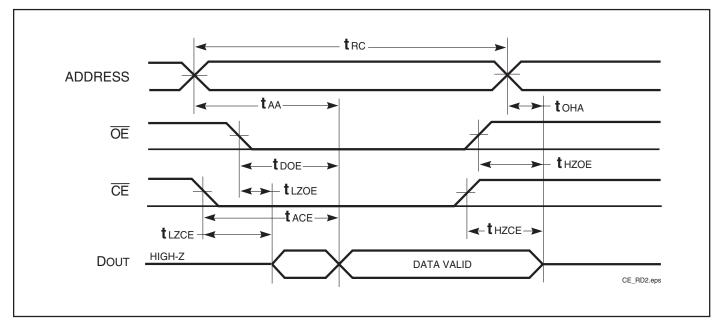


AC WAVEFORMS

READ CYCLE NO. $1^{(1,2)}$ (Address Controlled) ($\overline{CE} = \overline{OE} = V_{IL}$)



READ CYCLE NO. 2^(1,3) (\overline{CE} and \overline{OE} Controlled)



Notes:

- 1. WE is HIGH for a Read Cycle.
- 2. The device is continuously selected. \overline{OE} , $\overline{CE} = V_{IL}$.
- 3. Address is valid prior to or coincident with CE LOW transitions.

WRITE CYCLE SWITCHING CHARACTERISTICS^(1,2) (Over Operating Range)

		- 8	ns	-10	ns	
Symbol	Parameter	Min.	Max	Min.	Max.	Unit
twc	Write Cycle Time	8		10		ns
t SCE	CE to Write End	7		8		ns
taw	Address Setup Time to Write End	7		8		ns
tна	Address Hold from Write End	0	_	0	_	ns
tsa	Address Setup Time	0		0		ns
tpwe1	\overline{WE} Pulse Width (\overline{OE} = HIGH)	6	_	7	_	ns
tpwe2	\overline{WE} Pulse Width (\overline{OE} = LOW)	6.5	_	8	_	ns
tsd	Data Setup to Write End	4		5		ns
tнd	Data Hold from Write End	0	_	0	_	ns
thzwe ⁽³⁾	WE LOW to High-Z Output	_	3		4	ns
tlzwe ⁽³⁾	WE HIGH to Low-Z Output	0	_	0		ns

Notes:

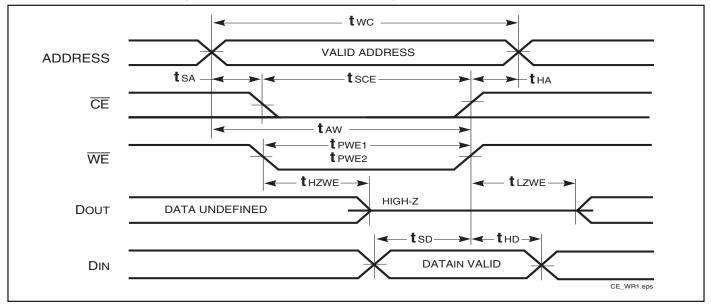
1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1.

The internal write time is defined by the overlap of CE LOW and WE LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.

3. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

WRITE CYCLE NO. 1^(1,2) (CE Controlled, OE = HIGH or LOW)

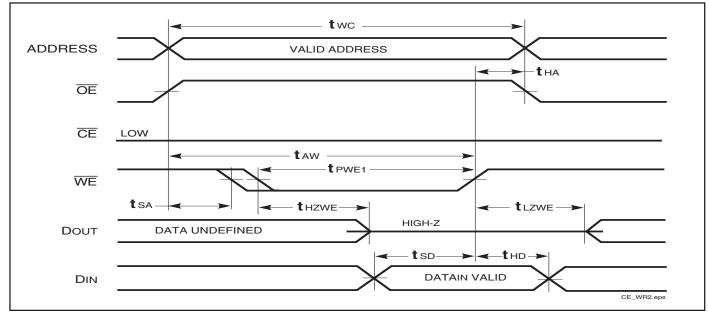


Note:

 The internal Write time is defined by the overlap of CE = LOW and WE = LOW. All signals must be in valid states to initiate a Write, but any can be deasserted to terminate the Write. The Data Input Setup and Hold timing is referenced to the rising or falling edge of the signal that terminates the Write.



AC WAVEFORMS

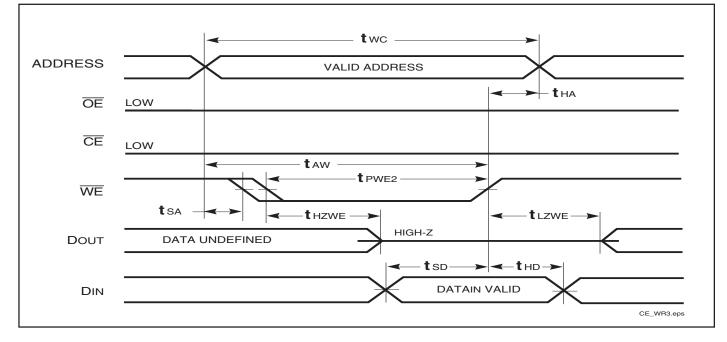


WRITE CYCLE NO. $2^{(1)}$ (WE Controlled, \overline{OE} = HIGH during Write Cycle)

Note:

The internal Write time is defined by the overlap of CE = LOW and WE = LOW. All signals must be in valid states to initiate a Write, but any can be deasserted to terminate the Write. The Data Input Setup and Hold timing is referenced to the rising or falling edge of the signal that terminates the Write.





Note:

The internal Write time is defined by the overlap of CE = LOW and WE = LOW. All signals must be in valid states to initiate a Write, but any can be deasserted to terminate the Write. The Data Input Setup and Hold timing is referenced to the rising or falling edge of the signal that terminates the Write.

ORDERING INFORMATION

Commercial Range: 0°C to +70°C

Speed (ns)	Order Part No.	Package
8	IS61LV2568L-8K IS61LV2568L-8T IS61LV2568L-8TL	400-mil SOJ TSOP (Type II) TSOP (Type II), Lead-free
10	IS61LV2568L-10T IS61LV2568L-10TL	TSOP (Type II) TSOP (Type II), Lead-free

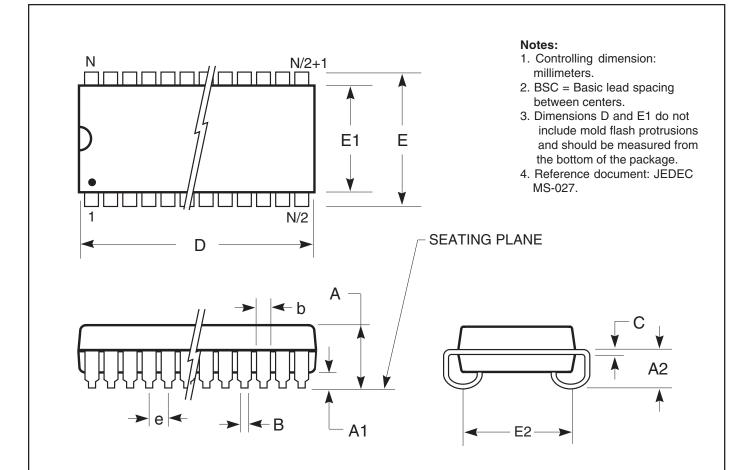
Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
10	IS61LV2568L-10KI	400-mil SOJ
	IS61LV2568L-10KLI	400-mil SOJ, Lead-free

PACKAGING INFORMATION



400-mil Plastic SOJ Package Code: K



Millim		eters	Inches		Millim	Millimeters		Inches		Millimeters		es
Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
No. Leads	(N)	28	8			32	2				36	
Α	3.25	3.75	0.128	0.148	3.25	3.75	0.128	0.148	3.25	3.75	0.128	0.148
A1	0.64	—	0.025	—	0.64	_	0.025	_	0.64	_	0.025	_
A2	2.08	_	0.082		2.08	—	0.082	—	2.08	—	0.082	_
В	0.38	0.51	0.015	0.020	0.38	0.51	0.015	0.020	0.38	0.51	0.015	0.020
b	0.66	0.81	0.026	0.032	0.66	0.81	0.026	0.032	0.66	0.81	0.026	0.032
С	0.18	0.33	0.007	0.013	0.18	0.33	0.007	0.013	0.18	0.33	0.007	0.013
D	18.29	18.54	0.720	0.730	20.82	21.08	0.820	0.830	23.37	23.62	0.920	0.930
E	11.05	11.30	0.435	0.445	11.05	11.30	0.435	0.445	11.05	11.30	0.435	0.445
E1	10.03	10.29	0.395	0.405	10.03	10.29	0.395	0.405	10.03	10.29	0.395	0.405
E2	9.40	BSC	0.370	BSC	9.40	BSC	0.370) BSC	9.40	BSC	0.370) BSC
е	1.27	BSC	0.05	D BSC	1.27 E	3SC	0.050) BSC	1.27	BSC	0.050) BSC

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PACKAGING INFORMATION



Millimeters		Inches		Millim	Millimeters		Inches		Millimeters		Inches	
Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
No. Leads	(N)	40)			2			44			
Α	3.25	3.75	0.128	0.148	3.25	3.75	0.128	0.148	3.25	3.75	0.128	0.148
A1	0.64	—	0.025	—	0.64	—	0.025	—	0.64	—	0.025	_
A2	2.08	—	0.082	—	2.08	_	0.082	—	2.08	_	0.082	_
В	0.38	0.51	0.015	0.020	0.38	0.51	0.015	0.020	0.38	0.51	0.015	0.020
b	0.66	0.81	0.026	0.032	0.66	0.81	0.026	0.032	0.66	0.81	0.026	0.032
С	0.18	0.33	0.007	0.013	0.18	0.33	0.007	0.013	0.18	0.33	0.007	0.013
D	25.91	26.16	1.020	1.030	27.18	27.43	1.070	1.080	28.45	28.70	1.120	1.130
E	11.05	11.30	0.435	0.445	11.05	11.30	0.435	0.445	11.05	11.30	0.435	0.445
E1	10.03	10.29	0.395	0.405	10.03	10.29	0.395	0.405	10.03	10.29	0.395	0.405
E2	9.40	BSC	0.370	BSC	9.40	BSC	0.370) BSC	9.40	BSC	0.370) BSC
е	1.27	BSC	0.05) BSC	1.27 E	BSC	0.050) BSC	1.27	BSC	0.050) BSC

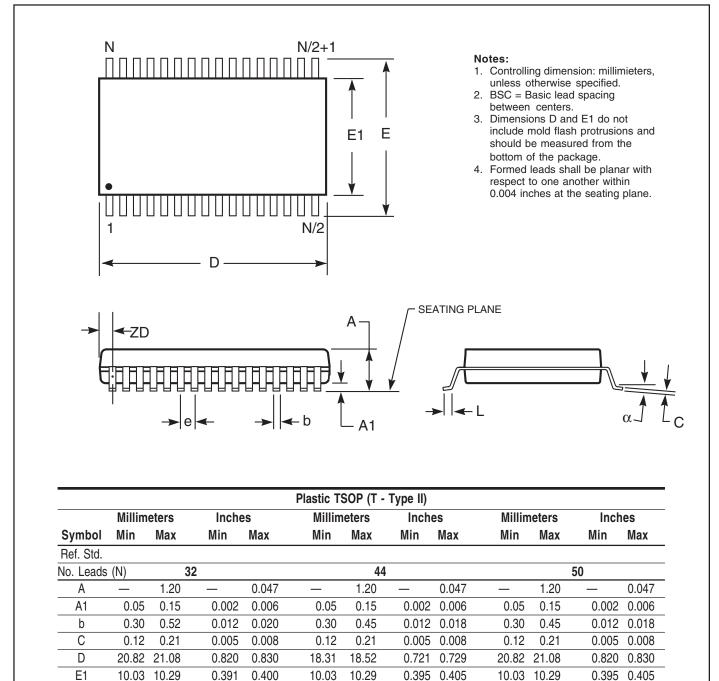
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PACKAGING INFORMATION



Plastic TSOP

Package Code: T (Type II)



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11.96

0.60

5°

0.455 0.471

0.016 0.024

0.032 REF

5°

0°

0.032 BSC

11.56 11.96

0.80 BSC

0.88 REF

0.60

5°

0.40

0°

0.455 0.471

0.016 0.024

0.035 REF

5°

0°

0.031 BSC

0.451

0.016

0°

0.050 BSC

0.037 REF

0.466

0.024

5°

11.56

0.41

0°

0.80 BSC

0.81 REF

Е

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ZD

α

11.56 11.96

1.27 BSC

0.95 REF

0.60

5°

0.40

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